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ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device includes a hetero-configuration having an active layer, a first clad layer, and a second clad layer, the active layer being interposed between the clad layers. The active layer emits light when charge carriers are injected. The first and second clad layers keep the injected charge carriers in the active layer. The hetero-configuration is interposed between a first and a second electrode. The semiconductor light emitting device further includes a dense defect-injected layer. This layer is provided between the first electrode and the hetero-configuration. The dense defect-injected layer is made of material more fragile than the hetero-configuration. The dense defect-injected layer prevents defects injected into the hetero-configuration.

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